

Variable gain RF predriver amplifier

SA910

DESCRIPTION

The SA910 is a variable gain predriver amplifier designed for handheld analog cellular telephones. When used with the Philips BLT61 UHF power transistor, it forms a cost-effective, low-profile, surface mount power amplifier solution (+32 with 55% efficiency +32dBm). The SA910 integrates power detection and control circuitry that is stabilized over temperature and voltage. In power down mode, the SA910 draws less than 10µA of current. The SA910 is fabricated using Philips QUBiC BiCMOS process.

FEATURES

- MMIC BiCMOS predriver amplifier
- Low voltage 2.7 to 5.5V single supply operation
- 820 to 905MHz bandwidth
- High power gain >20dB
- High power output >23dBm (typical) @ 3V
- Efficiency >35% (typical)
- Wide gain control range: >32dB
- Few external components required
- Integrated power detector and comparison gain control circuitry
- 50Ω input, open-collector output
- SSOP-20 package
- Integrated regulator with offset adjustment for biasing an external output stage

PIN CONFIGURATION

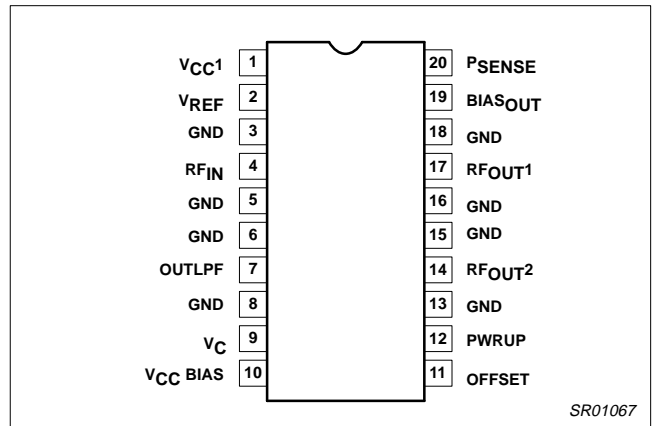


Figure 1. Pin Configuration

- Powerdown $I_{CC} < 0.5\mu A$

APPLICATIONS

- 900MHz analog cellular
- Handheld transmitting equipment in the 820 to 905MHz frequency range

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG #
20-Pin Plastic SSOP (Shrink Small Outline Package)	-40 to +85°C	SA910	SOT266-1

BLOCK DIAGRAM

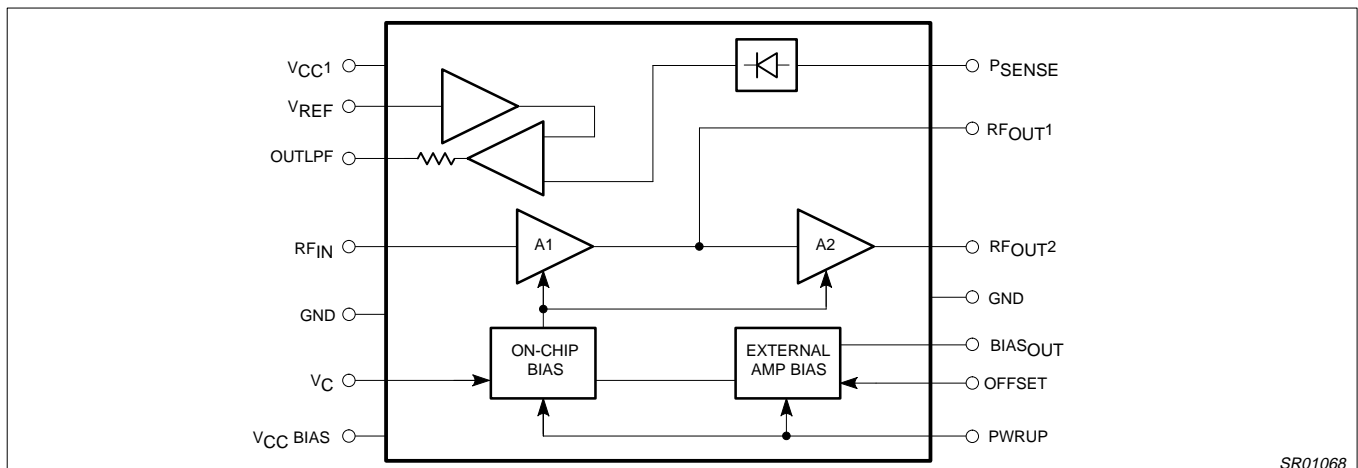


Figure 2. Block Diagram

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PIN DESCRIPTIONS

Pin No.	Mnemonic	Function
1	V _{CC1}	Power supply for power sense loop and off-chip bias
2	V _{REF}	Power sense reference voltage input
3	GND	Ground
4	RF _{IN}	Pre-driver input
5	GND	Ground
6	GND	Ground
7	OUTLPF	Power sense detected output
8	GND	Ground
9	VC	Gain control input
10	V _{CC} BIAS	Power supply for on-chip bias
11	OFFSET	External power amp bias offset adjustment
12	PWRUP	Power-up input
13	GND	Ground
14	RF _{OUT2}	Pre-driver output
15	GND	Ground
16	GND	Ground
17	RF _{OUT1}	Output of first stage
18	GND	Ground
19	BIAS _{OUT}	Output to bias external power amplifier stage
20	P _{SENSE}	Power sense input

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNITS
V _{CC1} /V _{CCBIAS}	DC supply voltages	-0.3 to +6.0	V
	Voltage applied to any other pin ¹	-0.3 to (V _{CC1} + 0.3)	V
P _D	Power dissipation	1.5	W
P _{IN}	Input drive power	5	mW
P _{DET}	Input detect power	20	mW
P _L	Load power	500	mW
T _{JMAX}	Maximum operating junction temperature	150	°C
T _{STG}	Storage temperature range	-65 to +150	°C

NOTES:

1. Except RF_{OUT1} and RF_{OUT2} which can have 8V max.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	RATING	UNITS
V _{CC1} /V _{CCBIAS}	Supply voltage	3 to 3.6	V
T _A	Operating ambient temperature range	-40 to +85	°C
T _J	Operating junction temperature	<125	°C

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AC ELECTRICAL CHARACTERISTICS
 $V_{CC1} = V_{CCBIAS} = +3V; V_{CC}(RF_{OUT1}, RF_{OUT2}) = 3.6V; T_A = 25^{\circ}C, Z_S = Z_L = 50\Omega; V_C = 2V; RF_{IN} = 1mW;$ unless otherwise stated.

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
f_{RF}	Frequency range		820	830	905	MHz
P_L	Load power at RF_{OUT2}	Saturated ¹		24.5		dBm
S_{21}	Small signal gain			31		dB
η	Efficiency	$P_L = 23dBm$		35		%
S_{11}	Return loss	Small signal input		-12		dBm
G_C	Gain control from V_C	$dP/dV < 120dB/V$	32			dB
S_{12}	Reverse isolation			-40		dB
GOFF	Gain at RF_{OUT2} during power-down ($RF_{IN} = -20dBm$)			-30		dB
PSENSE	Power detector range		-28	25	0	dBm

NOTE:

1. Needs proper matching.

DC ELECTRICAL CHARACTERISTICS
 $V_{CC1} = V_{CCBIAS} = +3V, V_{CC}(RF_{OUT1}, RF_{OUT2}) = 3.6V; T_A = 25^{\circ}C, Z_S = Z_L = 50\Omega;$; unless otherwise stated.

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNITS
			MIN	-3 σ	TYP	+3 σ	MAX	
V_{CC}	Power supply voltage range		2.7		3.0		5.5	V
I_{CC}	Total DC current from all V_{CC}	Pin 12 = HIGH; Pin 9 > V_{BE}					300	mA
I_{2B}	I_{CC} under zero bias mode	Pin 12 = HIGH; Pin 9 < V_{BE}					0.3	mA
I_{OFF}	Powerdown current	Pin 12 = low			0.5			μA
I_{PU}	Input current to PWRUP	Pin 12 = HIGH					100	μA
		Pin 12 = LOW					0	
V_{PU}	Input level for PWRUP (Pin 12)	Pin 12 = LOW	0				$0.3V_{CC}$	V
		Pin 12 = HIGH	$0.7V_{CC}$				V_{CC}	V
I_{REF}	Input current to V_{REF} (Pin 2)					1	μA	
V_{REF}	Power control reference voltage (Pin 1)		0			2.0	V	
V_{BIAS}	Bias-OUT voltage (Pin 19)	$V_C \geq 0.7V$			0.6			V
I_{BIAS}	DC current available @ Bias-OUT (Pin 19)		50					mA
V_C	Control voltage (Pin 9) range		0				2	V
I_{VC}	Input current to V_C (Pin 9)						0.5	mA
t_{ON}	Power up time				20			μs
t_{OFF}	Power down time				20			μs
	Power up settling time				100			μs